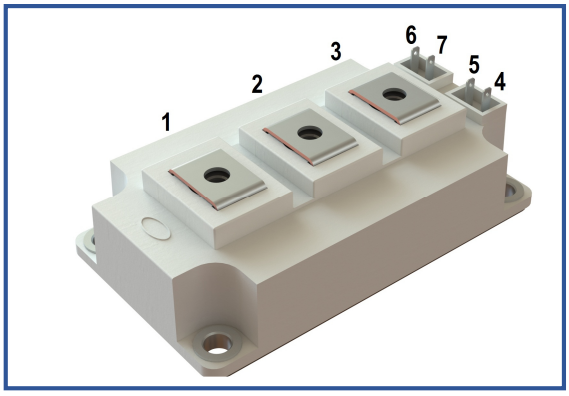
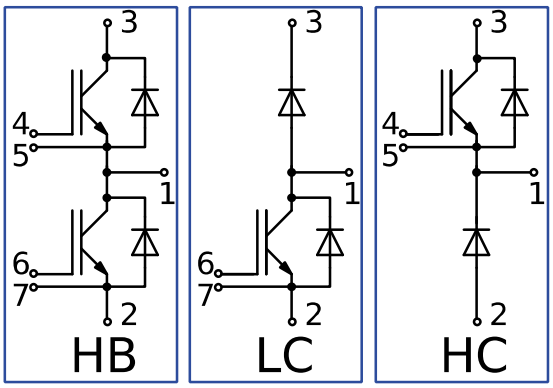
Industry standart 62mm IGBT module

1200 V 200 A





Chip features

- IGBT chip
  - Trench FS — V-Series IGBT (6 th gen)
  - low $V_{CE(sat)}$ value
  - 10 µs short circuit of 150°C
  - square RBSOA of 2xI_C
  - low EMI
- FRD chip
  - fast and soft reverse recovery
  - low voltage drop

Design features

- copper baseplate
- Al_2O_3 DBC substrate
- ultrasonically welded power terminals
- Improved termal cycling
- RoHS compliant

Typical application

- AC motor drivers
- solar inverter
- air conditioning
- high power converters and UPS

Maximum rated values

Definition	Symbol	Conditions	Value	Unit
IGBT				
Collector-Emitter voltage	V_{CES}	V_{GE} = 0.	1200	V
Collector current (nominal)	$I_{C\ nom}$		200	A
Collector current (maximum continuous)	$I_{C\ 25}$	$T_{vj\ (max)}$ = 175°C; T_c = 25°C.	301	A
	$I_{C\ 80}$	$T_{vj\ (max)}$ = 175°C; T_c = 80°C.	231	A
Repetitive peak collector current*1	I_{CRM}	I_{CRM} = 3 x $I_{C\ nom}$; t_p = 1 ms.	600	A
Short-circuit duration	t_{psc}	T_{vj} = 25°C; V_{GE} = ±15 V; V_{CE} = 720 V; $R_{G\ on}$ = $R_{G\ off}$ = 3 Ω; $I_{C\ max}$ < 1200 A.	10	µs
		T_{vj} = 150°C; V_{GE} = ±15 V; V_{CE} = 720 V; $R_{G\ on}$ = $R_{G\ off}$ = 3 Ω; $I_{C\ max}$ < 1100 A.	10	
Gate-Emitter voltage	V_{GES}		±20	V
Junction operating temperature	$T_{vj\ (op)}$		-40…+150	°C
Inverse diode \ Freewheeling diode				
Repetitive peak reverse voltage	V_{RRM}	V_{GE} = 0 V.	1200	V
Forward current (nominal)	$I_{F\ nom}$		200	A
Forward current (maximum continuous)	$I_{F\ 25}$	$T_{vj\ (max)}$ = 175°C; T_c = 25°C.	221	A
	$I_{F\ 80}$	$T_{vj\ (max)}$ = 175°C; T_c = 80°C.	167	A
Repetitive peak forward current*1	I_{FRM}	I_{FRM} = 3 x $I_{F\ nom}$; t_p = 1 ms.	600	A
Junction operating temperature	$T_{vj\ (op)}$		-40…+150	°C
Module				
Storage temperature	T_{stg}		-40…+50	°C
Isolation voltage	V_{isol}	AC sin 50 Hz; t = 1 min.	4000	V

*1 Pulse width and repetition rate should be such that device junction temperature does not exceed maximum T_{vj} rating.

Characteristics

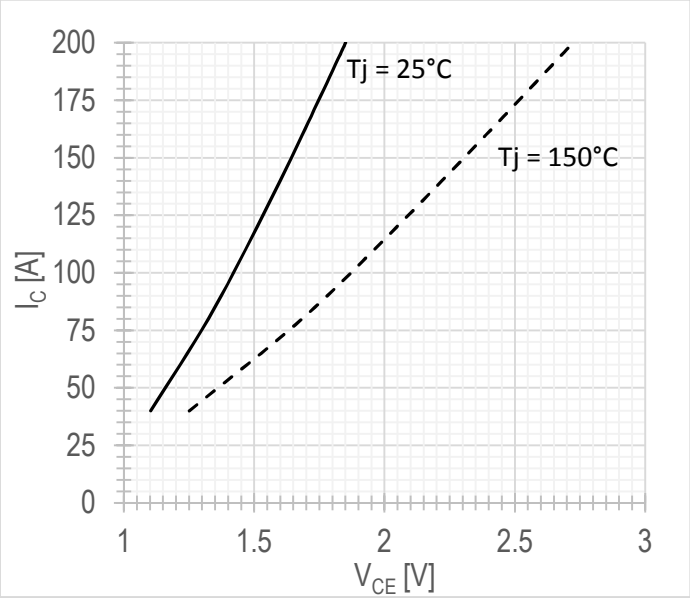
Definition	Symbol	Conditions		Value min.	Value typ.	Value max.	Unit
IGBT							
Collector-Emitter saturation voltage	V_{CEsat}	V_{GE} = +15 V; I_C = 200 A; t_u = 1000 µs.	T_{vj} = 25°C	1.81	1.83	2.02	V
			T_{vj} = 150°C	2.39	2.47	2.75	V
Gate-Emitter threshold voltage	$V_{GE(th)}$	I_C = 8 mA; V_{CE} = V_{GE}; T_{vj} = 25°C; t_u = 2 ms.		5.50	6.05	6.50	V
Collector-Emitter cut-off current	I_{CES}	V_{CE} = 1200 V; t_u = 10 ms; V_{GE} = 0.	T_{vj} = 25°C	2.35	2.98	150	µA
			T_{vj} = 150°C	1.09	1.22	2.50	mA
Gate-Emitter leakage current	I_{GES}	V_{CE} = 0; V_{GE} = ±20 V; T_{vj} = 25°C; t_u = 30 ms.		14.9	16.5	200	nA
Input capacitance	C_{ies}	V_{CE} = 10 V; V_{GE} = 0 V; f = 1 MHz; T_{vj} = 25°C.		-	18.2	-	nF
Output capacipance	C_{oes}			-	1.40	-	nF
Reverse transfer capacitance	C_{res}			-	1.60	-	nF
Total gate charge	Q_G	I_C = 200 A; V_{CE} = 600 V; V_{GE} = - 8÷15 V.		-	2078	2192	nC
Internal gate resistance	R_{Gint}	T_{vj} = 25°C.		-	3.75		Ω
Turn-on delay time	$t_{d(on)}$	V_{CE} = 600 V; V_{GE} = ±15 V; $I_{C\,max}$ = 200 A; R_G = 3 Ω; L = 300 µH.	T_{vj} = 25°C	368	373	410	ns
			T_{vj} = 150°C	406	412	450	
Rise time	t_{ri}		T_{vj} = 25°C	50.0	50.9	56.0	ns
			T_{vj} = 150°C	54.0	55.9	58.0	
Turn-on energy	E_{on}		T_{vj} = 25°C	6.60	7.93	10.0	mJ
			T_{vj} = 150°C	13.7	15.5	18.0	
Turn-off delay time	$t_{d(off)}$		T_{vj} = 25°C	446	451	490	ns
			T_{vj} = 150°C	514	522	575	
Fall time	t_{fi}		T_{vj} = 25°C	176	223	280	ns
			T_{vj} = 150°C	301	319	360	
Turn-off energy	E_{off}		T_{vj} = 25°C	16.6	17.0	19.0	mJ
			T_{vj} = 150°C	21.6	22.3	24.6	
Collector-emitter threshold voltage	V_{CE0}	V_{GE} = +15 V; T_{vj} = 150°C; I_{CE1} = 50 A; I_{CE2} = 200 A; t_u = 1000 µs.		0.85	0.86	0.90	V
On-State slope resistance (IGBT)	r_{CE0}			7.67	8.04	9.14	mΩ
Thermal resistance junction to case	$R_{th(j-c)}$	DC; I_{CE} = 200±20 A; I_{test} = 1.0 A; V_{GE} = +15 V.		-	0.086	0.140	K/W
Inverse diode \ Freewheeling diode							
Forward voltage drop	V_F	I_F = 200 A; V_{GE} = 0; t_u = 500 µs.	T_{vj} = 25°C	1.86	2.02	2.25	V
			T_{vj} = 150°C	2.01	2.20	2.50	V
Reverse recovery time	t_{rr}	V_{GE} = ±15 V; V_{CE} = 600 V; $I_{C\,max}$ = 200 A; $R_{G\,on}$ = 3 Ω; L = 300 µH.	T_{vj} = 25°C	102	108	125	ns
			T_{vj} = 150°C	281	322	400	ns
Repetitive peak reverse current	I_{RRM}		T_{vj} = 25°C	160	171	205	A
			T_{vj} = 150°C	202	214	260	A
Reverse recovered charge	Q_{rr}		T_{vj} = 25°C	10.9	11.6	14.5	µC
			T_{vj} = 150°C	23.6	25.8	33.0	µC
Reverse recovery energy	E_{rec}		T_{vj} = 25°C	5.17	5.94	7.35	mJ
			T_{vj} = 150°C	10.1	11.5	15.0	mJ
Threshold voltage	$V_{(T0)}$	T_{vj} = 150°C; V_{GE} = 0; I_{CE1} = 50 A; I_{CE2} = 200 A; t_u = 1000 µs.		0.83	0.84	0.89	V
Forward slope resistance	r_T			5.87	6.79	8.00	mΩ
Thermal resistance junction to case	$R_{th(JC-D)}$	DC; I_{CE} = 180±20 A; I_{test} = 1.0 A; V_{GE} = +15 V.		-	0.196	0.260	K/W

Module							
Pin resistance	R_{Pxy}	T_{vj} = 25°C.	R_{P12}	-	0.28	0.50	mΩ
			R_{P13}	-	0.38	0.50	
Parasitic inductance between terminals	L_{Pxy}	T_{vj} = 25°C; f = 1 MHz.	L_{P12}	-	33.4	35.0	nH
			L_{P13}	-	56.0	60.0	
Thermal resistance case to heatsink	R_{thCH}	per module		-	0.02	0.04	K/W
Mounting torque for screws to heatsink	M_s	to heatsink M6		3.00	-	5.00	N*m
Mounting torque for terminal screws	M_t	to terminals M5		2.25	2.50	2.75	N*m
Weight	W			-	320	340	g

Notes:

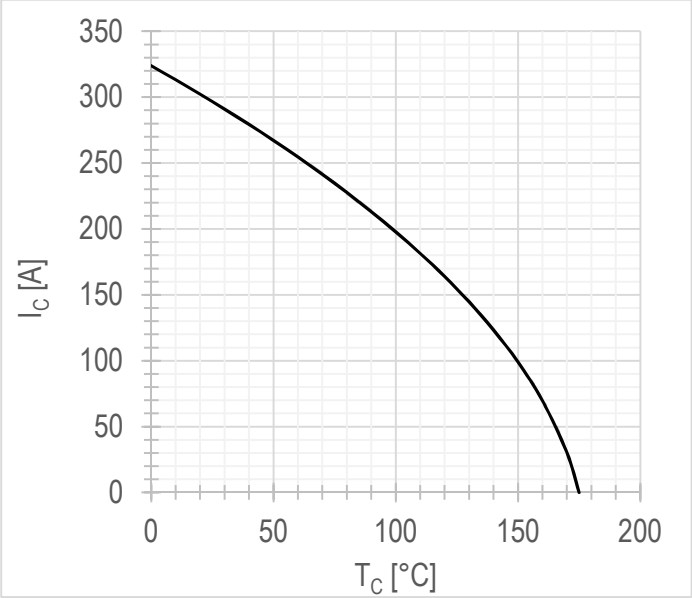
- Insulating material operating temperature 125°C max;
- Case temperature 125°C max;
- The recommended operating junction temperature $T_{vj\ op}$ = - 40 ÷ +150°C.

Chart 1 – typ. output characteristic, IGBT.



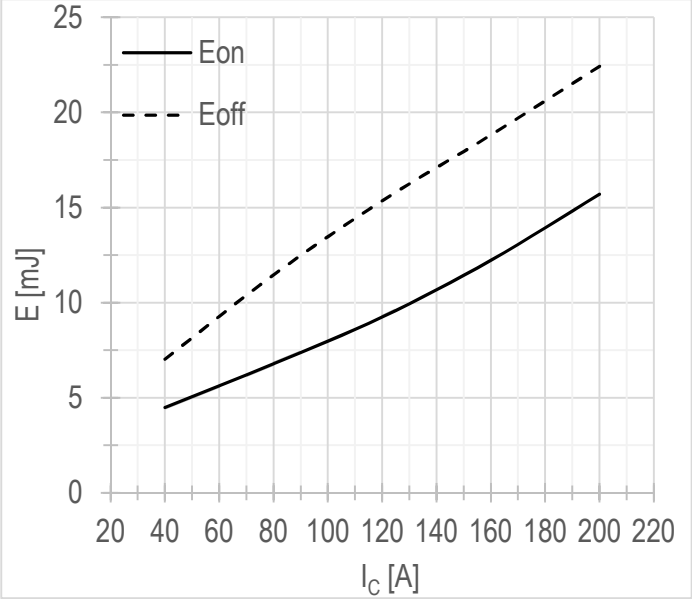
V_{GE} = +15 V.

Chart 2 – typ. rated current vs temperature.



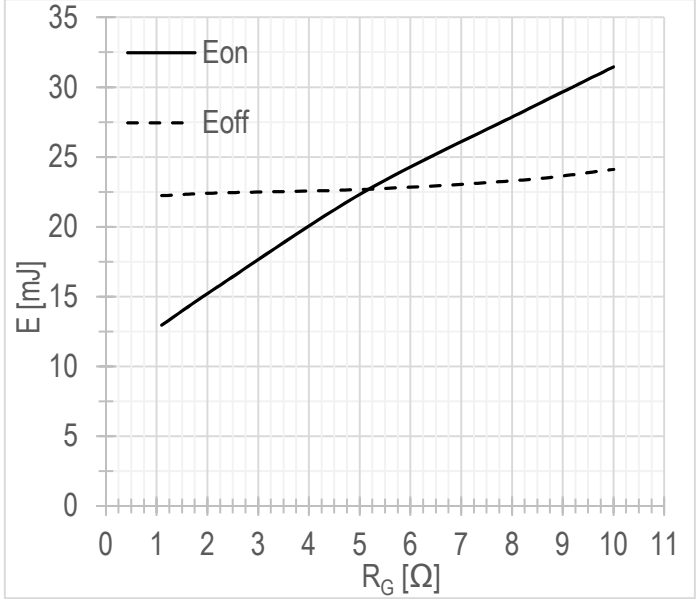
DC;
V_{GE} = +15 V;
$T_{vj\ (max)}$ = 150°C.

Chart 3 – typ. turn-on/-off energy vs rated current, IGBT.



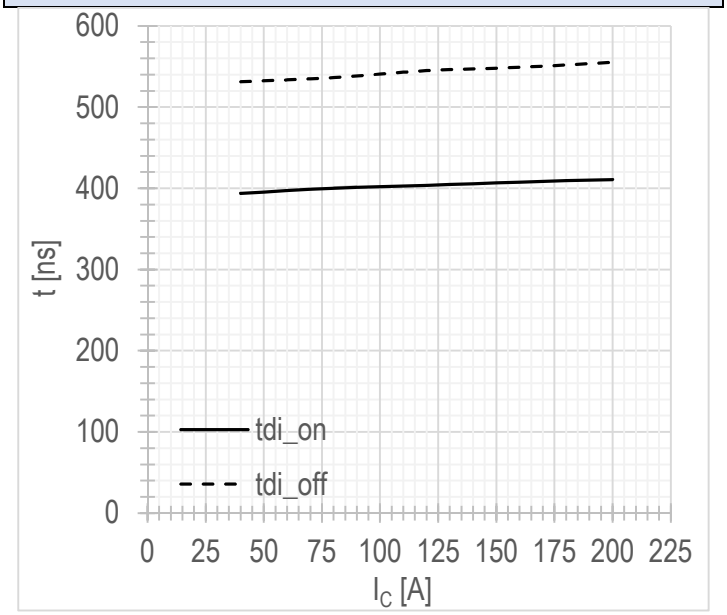
V_{CE} = 600 V;
V_{GE} = ±15 V;
R_G = 3 Ω;
L = 300 µH;
$T_{vj\ (max)}$ = 150°C.

Chart 4 – typ. turn-on/-off energy vs gate resistance, IGBT.



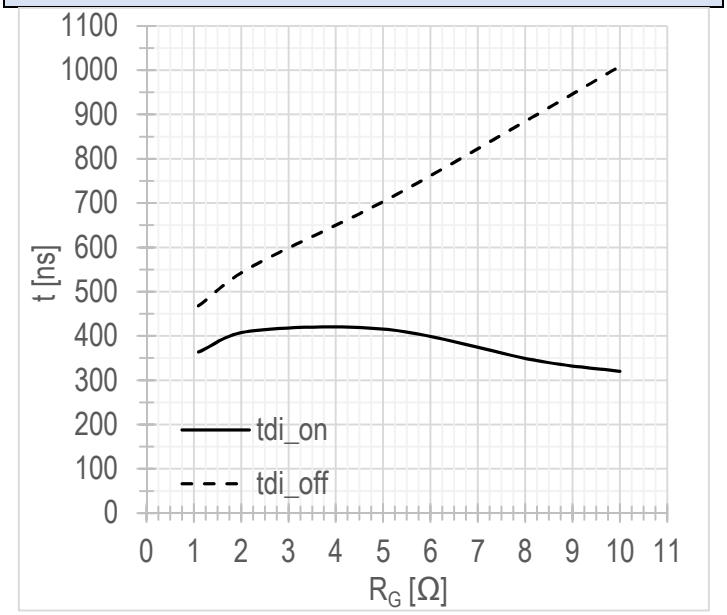
V_{CE} = 600 V;
V_{GE} = ±15 V;
I_{Cmax} = 200 A;
L = 300 µH;
$T_{vj\ (max)}$ = 150°C.

Chart 5 – typ. switching times vs rated current, IGBT.



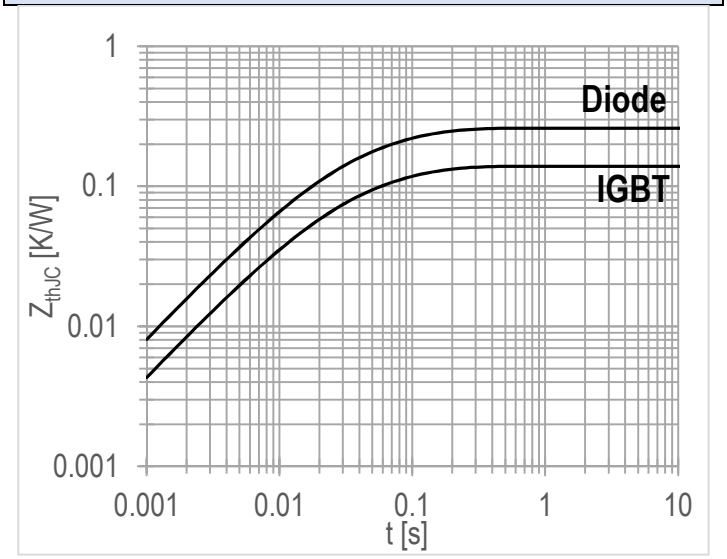
V_{CE} = 600 V;
V_{GE} = ±15 V;
R_G = 3.0 Ω;
L = 300 µH;
$T_{vj\ (max)}$ = 150°C.

Chart 6 – typ. switching times vs gate resistance, IGBT.



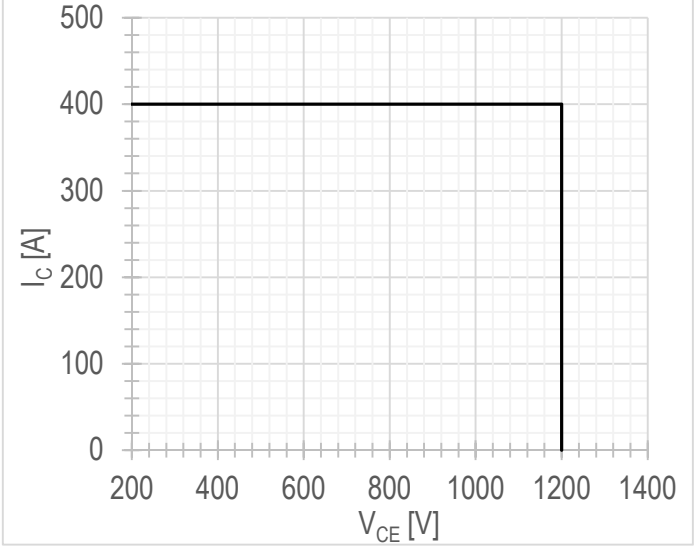
V_{CE} = 600 V;
V_{GE} = ±15 V;
$I_{C\ max}$ = 200 A;
L = 300 µH;
$T_{vj\ (max)}$ = 150°C.

Chart 7 – max. transient thermal impedance .



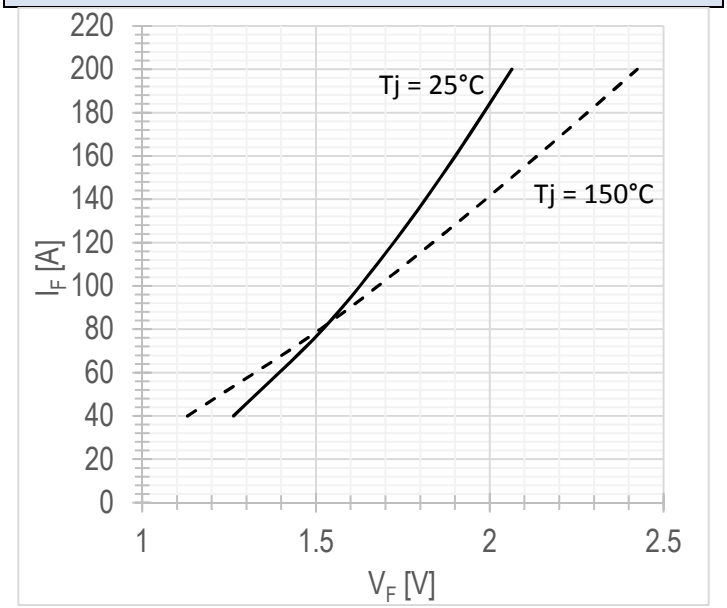
Single pulse;
V_{GE} = +15 V.

Chart 8 – RBSOA.



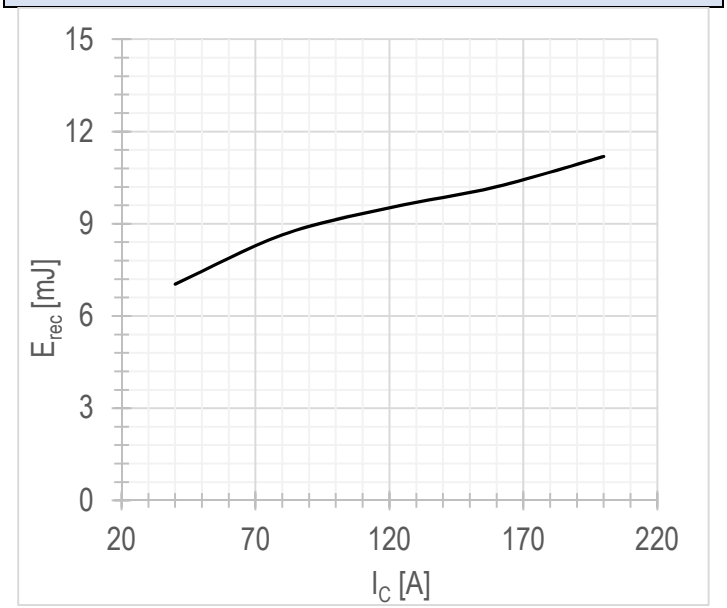
$V_{CE\ max}$ = 1200 V;
V_{GE} = ±15 V;
$I_{C\ max}$ = 2*$I_{C\ nom}$;
R_G = 2.2 Ω;
L = 100 µH.

Chart 9 – typ. output characteristic, FRD.



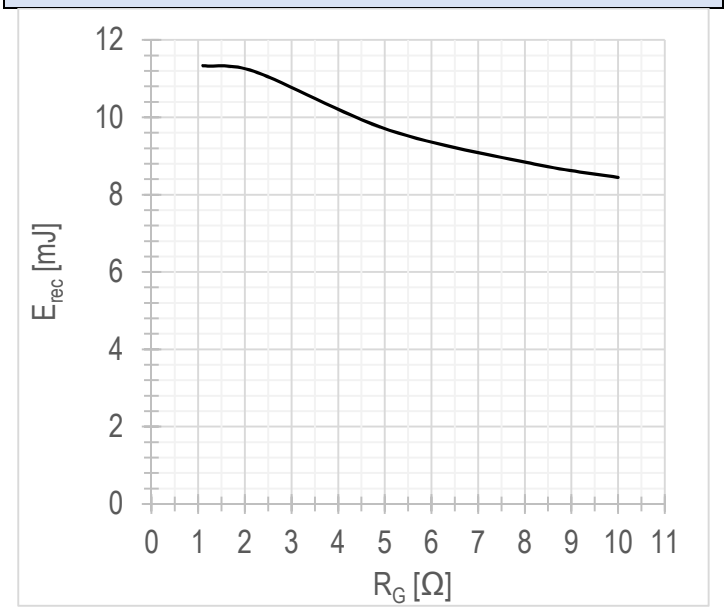
V_{GE} = +15 V.

Chart 10 – typ. swithing losses vs rated current, FRD.



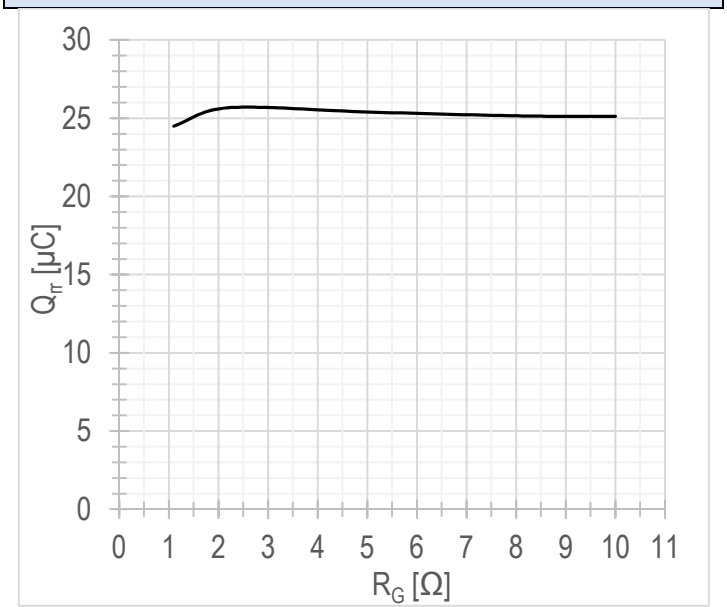
V_{GE} = ±15 V;
V_{CE} = 600 V;
L = 300 µH;
$R_{G\,on}$ = 3 Ω;
$T_{vj\,(max)}$ = 150°C.

Chart 11 – typ. swithing losses vs gate resistanse, FRD.



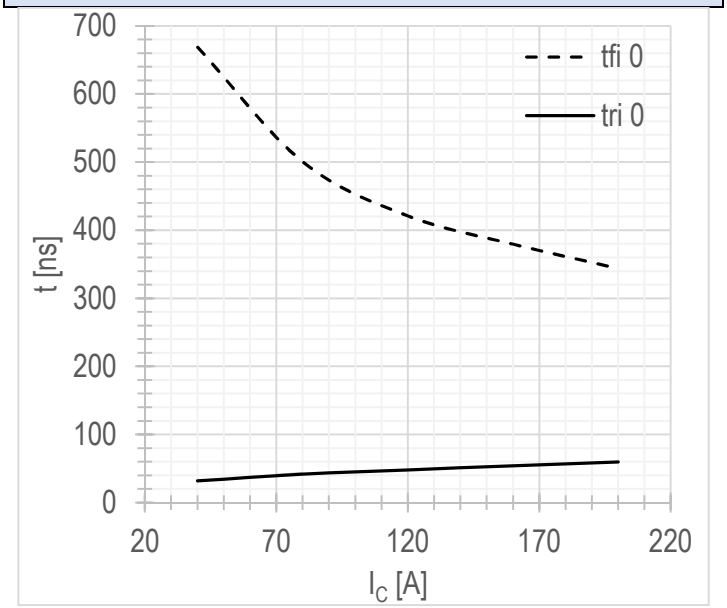
V_{GE} = ±15 V;
V_{CE} = 600 V;
$I_{C\,max}$ = 200 A;
L = 300 µH;
$T_{vj\,(max)}$ = 150°C.

Chart 12 – typ. reverse recovered charge vs gate resistance, FRD.



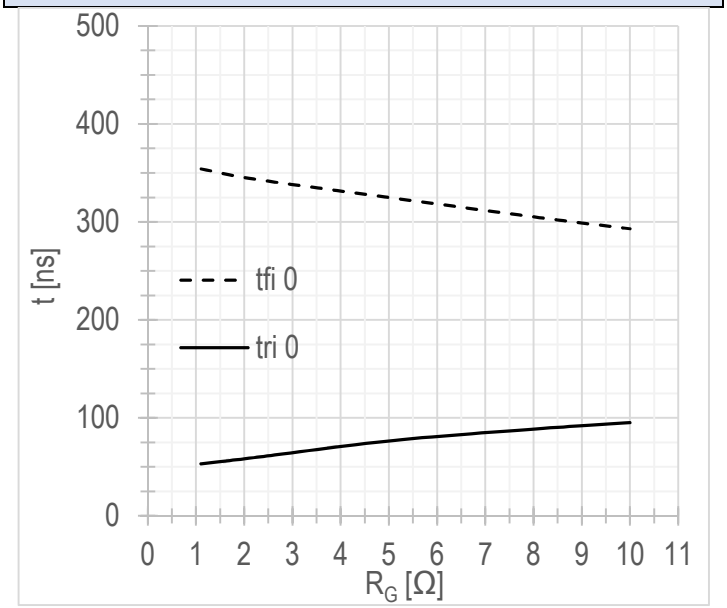
V_{GE} = ±15 V;
V_{CE} = 600 V;
$I_{C\,max}$ = 200 A;
L = 300 µH;
$T_{vj\,(max)}$ = 150°C.

Chart 13 – typ. switching times vs rated current, FRD.



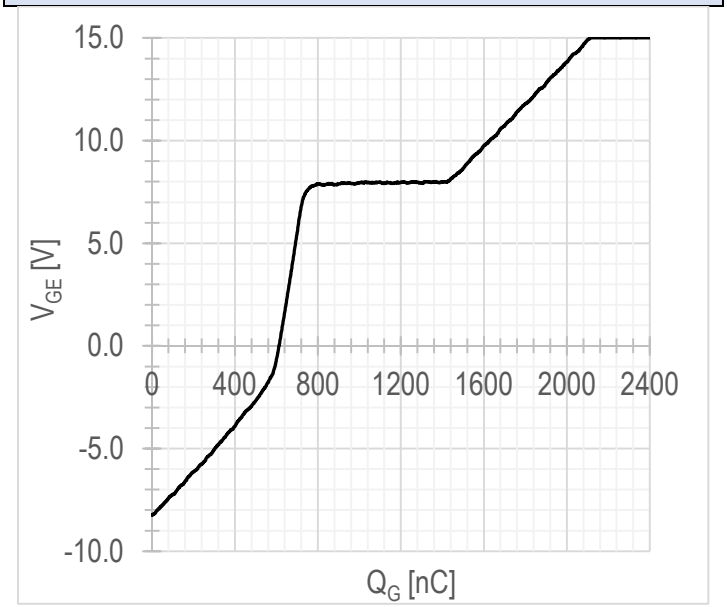
V_{CE} = 600 V;
V_{GE} = ±15 V;
R_G = 3 Ω;
L = 300 µH.
$T_{vj\ (max)}$ = 150°C.

Chart 14 – typ. switching times vs gate resistance, FRD.



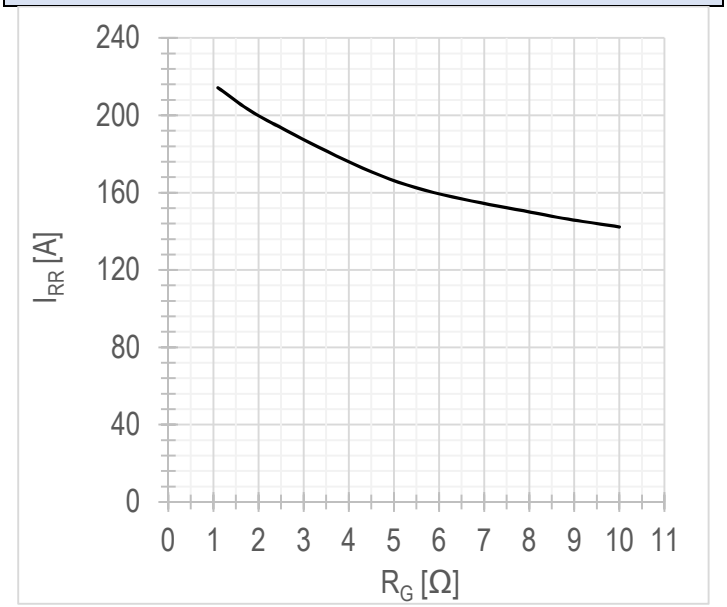
V_{CE} = 600 V;
V_{GE} = ±15 V;
$I_{C\ max}$ = 200 A;
L = 300 µH.
$T_{vj\ (max)}$ = 150°C.

Chart 15 – typ. gate charge characteristic.



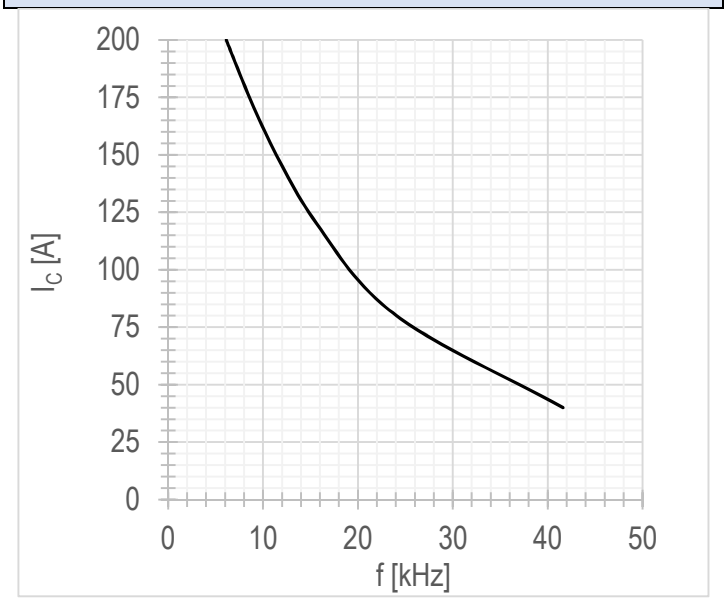
I_C = 200 A;
V_{CE} = 600 V;
V_{GE} = - 8÷15 V.

Chart 16 – typ. reverce recovery current vs gate resistance FRD.



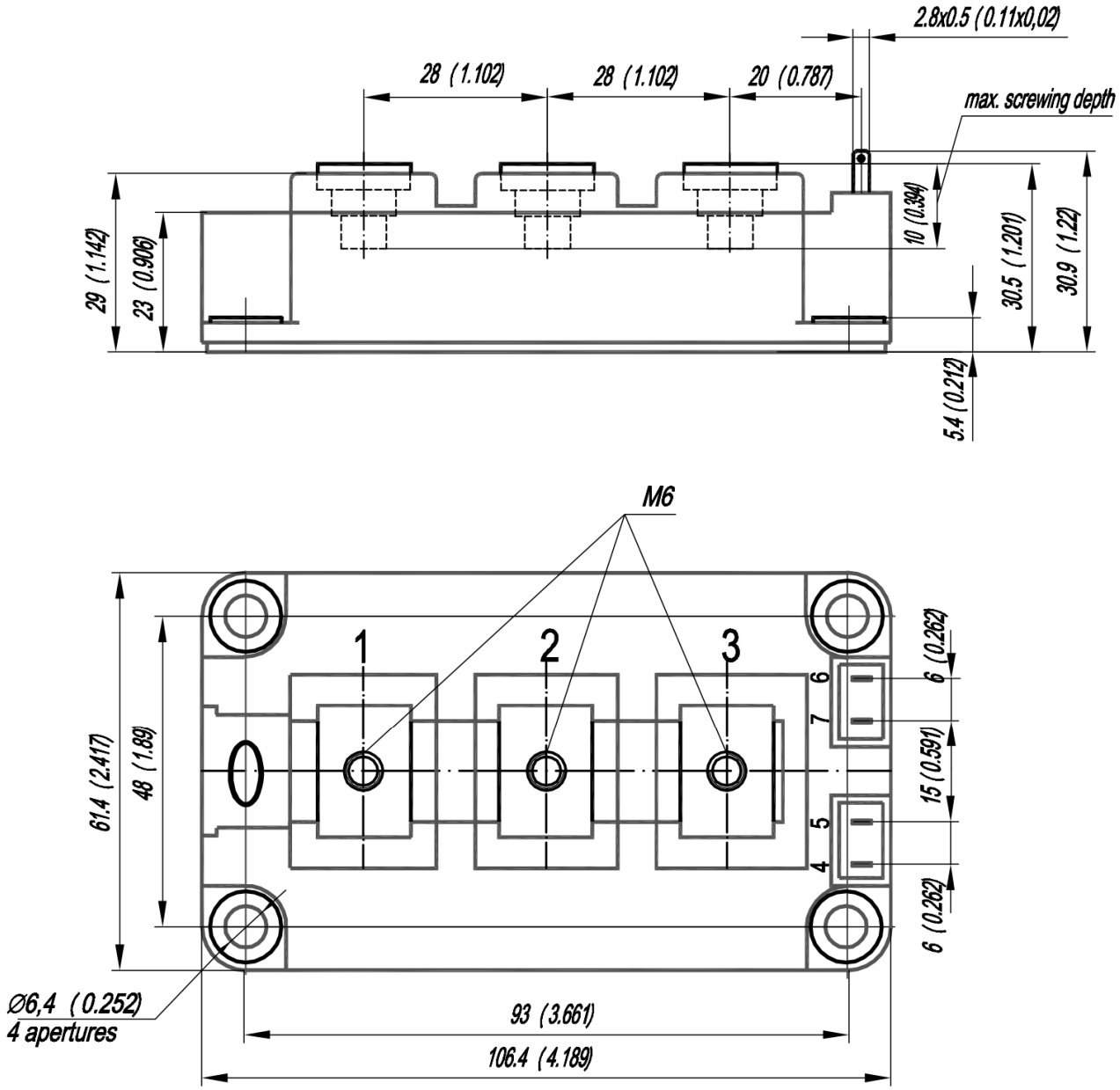
V_{CE} = 600 V;
V_{GE} = ±15 V;
L = 300 µH.
$T_{vj\ (max)}$ = 150°C.

Chart 17 – typ. rated current vs frequency.



Duty cycle 50%

Overall dimensions: Package type – AA



Part numbering guide

MIAA	-	HB	12	AA	-	200	N	
MIAA								IGBT module package type: AA
		HB						2 switches as Half-Bridge
		HC						1 switch as High-Side chopper
		LC						1 switch as Low-Side chopper
			12					Voltage rating (V_{CES}/100)
				AA				IGBT+FRD chipset modification
						200		Current Rating
							N	Climatic version: normal climate